Title (en)

SEMICONDUCTOR CERAMIC COMPOSITION AND METHOD FOR PRODUCING THE SAME

Title (de)

HALBLEITERKERAMIKZUSAMMENSETZUNG UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

COMPOSITION DE CÉRAMIQUE SEMI-CONDUCTRICE ET PROCÉDÉ DE PRODUCTION DE CETTE COMPOSITION

Publication

**EP 2096092 A1 20090902 (EN)**

Application

**EP 07830694 A 20071026**

Priority

- JP 2007070960 W 20071026
- JP 2006293366 A 20061027
- JP 2006298306 A 20061101

Abstract (en)

It is intended to provide a Pb-free semiconductor ceramic composition capable of shifting its Curie temperature toward a positive direction and capable of enhancing its jump characteristic while minimizing the increase in the resistivity at room temperature. There is provided a semiconductor ceramic composition in which a part of Ba of $BaTiO_3$ is substituted with Bi-Na, the semiconductor ceramic composition being obtained by sintering a mixed calcined powder containing a calcined BT powder containing a calcined powder of $(BaR)TiO_3$ or a calcined powder of $Ba(TiM)O_3$ (in which R and M each are a semiconductor dopant), and a calcined BNT powder containing a calcined powder of $(BiNa)TiO_3$ ; in which $BaCO_3$ and/or $TiO_2$ is/are added to the calcined BT powder or the calcined BNT powder or to the mixed calcined powder.

IPC 8 full level

**C04B 35/46** (2006.01); **H01C 7/02** (2006.01)

CPC (source: EP KR US)

**C01G 23/003** (2013.01 - EP US); **C01G 23/006** (2013.01 - EP US); **C01G 29/006** (2013.01 - EP US); **C04B 35/46** (2013.01 - KR); **C04B 35/4682** (2013.01 - EP US); **C04B 35/62675** (2013.01 - EP US); **C04B 35/62685** (2013.01 - EP US); **H01C 7/02** (2013.01 - KR); **H01C 7/025** (2013.01 - EP US); **H01C 7/045** (2013.01 - EP US); **H01C 17/06533** (2013.01 - EP US); **H01G 4/1227** (2013.01 - EP US); **H01G 7/06** (2013.01 - EP US); **H01L 21/02197** (2013.01 - EP); **H01L 21/31691** (2016.02 - US); C01P 2002/54 (2013.01 - EP US); C01P 2002/72 (2013.01 - EP US); C01P 2006/40 (2013.01 - EP US); C04B 2235/3201 (2013.01 - EP US); C04B 2235/3208 (2013.01 - EP US); C04B 2235/3227 (2013.01 - EP US); C04B 2235/3236 (2013.01 - EP US); C04B 2235/3251 (2013.01 - EP US); C04B 2235/3294 (2013.01 - EP US); C04B 2235/3298 (2013.01 - EP US); C04B 2235/3418 (2013.01 - EP US); C04B 2235/5436 (2013.01 - EP US); C04B 2235/608 (2013.01 - EP US); C04B 2235/656 (2013.01 - EP US); C04B 2235/6565 (2013.01 - EP US); C04B 2235/6567 (2013.01 - EP US); C04B 2235/6584 (2013.01 - EP US); H01L 28/20 (2013.01 - EP US)

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Designated contracting state (EPC)

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DOCDB simple family (application)

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